Philips Semiconductors

Product specification

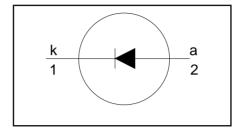
Rectifier diodes Schottky barrier

PBYR1645 series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{F(AV)} = 16 \text{ A}$
 $V_F \le 0.57 \text{ V}$

GENERAL DESCRIPTION

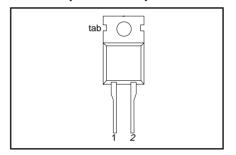
Schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR1645 series is supplied in the conventional leaded SOD59 (TO220AC) package.

PINNING

| PIN | DESCRIPTION | |
|-----|-------------|--|
| 1 | cathode | |
| 2 | anode | |
| tab | cathode | |
| | | |
| | | |

SOD59 (TO220AC)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | | UNIT |
|--------------------|---------------------------------------|--|------|------|----------|--------|
| | | PBYR16 | | 40 | 45 | |
| V_{RRM} | Peak repetitive reverse voltage | | - | 40 | 45 | V |
| V_{RWM} | Working peak reverse voltage | | - | 40 | 45 | V |
| V_R | Continuous reverse voltage | T _{mb} ≤ 116 °C | - | 40 | 45 | V |
| I _{F(AV)} | Average rectified forward current | square wave; $\delta = 0.5$; $T_{mb} \le 131$ °C | - | 1 | 6 | А |
| I _{FRM} | Repetitive peak forward current | square wave; $\delta = 0.5$; $T_{mb} \le 131$ °C | - | 3 | 2 | A |
| I _{FSM} | Non-repetitive peak forward current | t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM}(\text{max})}$ | - | | 35 50 | A A |
| I _{RRM} | Peak repetitive reverse surge current | pulse width and repetition rate limited by T _{i max} | - | , | 1 | Α |
| T _j | Operating junction temperature | J | - | 15 | 50 | °C |
| T_{stg} | Storage temperature | | - 65 | 17 | 75 | °C |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------------|---|-------------|------|------|------|------|
| R _{th j-mb} | Thermal resistance junction | | - | - | 1.5 | K/W |
| R _{th i-a} | to mounting base Thermal resistance junction to ambient | in free air | - | 60 | - | K/W |

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ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------|----------------------|--|------|------|------|------|
| V_{F} | Forward voltage | I _F = 16 A; T _i = 125°C | - | 0.53 | 0.57 | V |
| | | $I_{\rm F} = 16 {\rm A}$ | - | 0.55 | 0.63 | V |
| I_R | Reverse current | $\dot{V}_{R} = V_{RWM}$ | - | 0.2 | 1.7 | mΑ |
| | | $V_{R} = V_{RWM}$; $T_{j} = 100^{\circ}C$ | - | 27 | 40 | mΑ |
| C _d | Junction capacitance | $V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_j = 25 \text{ °C to } 125 \text{ °C}$ | - | 470 | - | pF |

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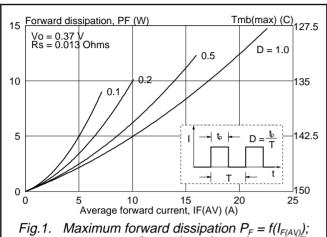


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

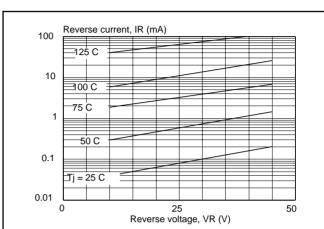


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter T_i

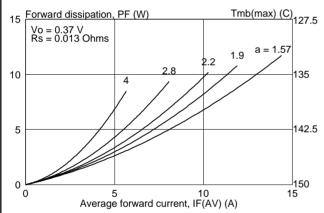
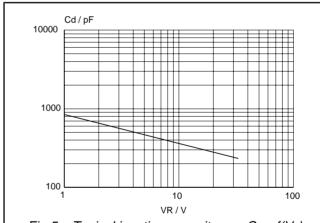


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where $a = f(I_{F(AV)})$; $factor = I_{F(RMS)} / I_{F(AV)}$.



Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125°C.

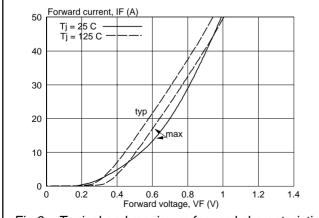


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

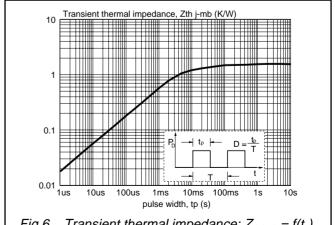
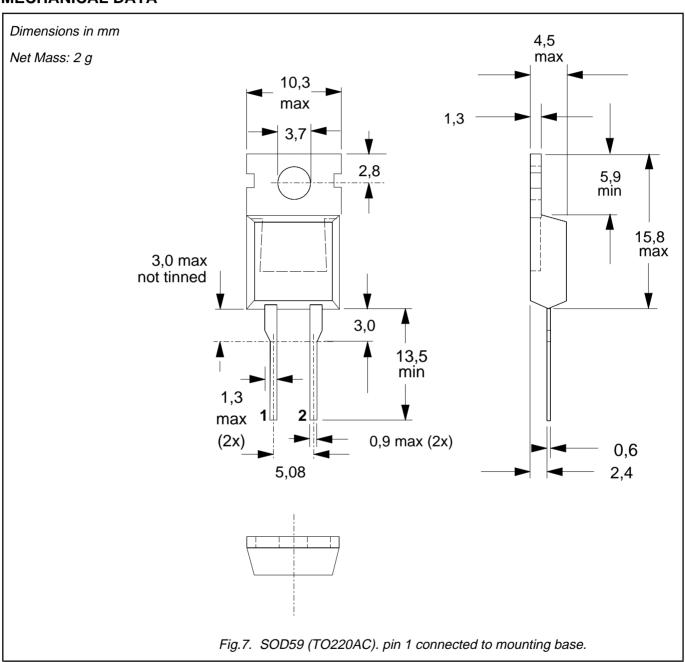


Fig.6. Transient thermal impedance; $Z_{th j-mb} = f(t_p)$.

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MECHANICAL DATA



- Refer to mounting instructions for TO220 envelopes.
 Epoxy meets UL94 V0 at 1/8".



Philips Semiconductors Product specification

Rectifier diodes PBYR1645 series Schottky barrier

DEFINITIONS

| Data sheet status | | | | |
|--|---|--|--|--|
| Objective specification | This data sheet contains target or goal specifications for product development. | | | |
| Preliminary specification | Preliminary specification This data sheet contains preliminary data; supplementary data may be published late | | | |
| Product specification This data sheet contains final product specifications. | | | | |
| Limiting values | | | | |

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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